

INTERNATIONAL SEARCH REPORT

International Application No

PCT/EP 03/03136

A. CLASSIFICATION OF SUBJECT MATTER

IPC 7 C30B25/02 H01L21/205

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 7 C30B H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

INSPEC, EPO-Internal

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	<p>BAUER M ET AL: "Relaxed SiGe buffers with thicknesses below 0.1 µm"</p> <p>THIN SOLID FILMS, ELSEVIER-SEQUOIA S.A. LAUSANNE, CH,</p> <p>vol. 369, no. 1-2, July 2000 (2000-07), pages 152-156, XP004200345</p> <p>ISSN: 0040-6090</p> <p>cited in the application</p> <p>page 153, left-hand column, paragraph 2</p> <p>-page 154, left-hand column, line 5</p> <p style="text-align: center;">--- -/-</p>	18-22

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier document but published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

19 November 2003

Date of mailing of the international search report

27/11/2003

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT		
Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	HACKBARTH T ET AL: "Alternatives to thick MBE-grown relaxed SiGe buffers" THIN SOLID FILMS, ELSEVIER-SEQUOIA S.A. LAUSANNE, CH, vol. 369, no. 1-2, July 2000 (2000-07), pages 148-151, XP004200344 ISSN: 0040-6090 the whole document	1-22
A	ROSENBLAD C ET AL: "A plasma process for ultrafast deposition of SiGe graded buffer layers" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS. NEW YORK, US, vol. 76, no. 4, 24 January 2000 (2000-01-24), pages 427-429, XP002200819 ISSN: 0003-6951 page 427, right-hand column, paragraph 2 -page 428, left-hand column, last line	1-22
A	US 2002/056414 A1 (LEE SEUNG-YUN ET AL) 16 May 2002 (2002-05-16) paragraphs '0023!', '0026!', '0077!'-'0079!	1-22
A	US 2002/139996 A1 (JAGANNATHAN BASANTH) 3 October 2002 (2002-10-03) paragraphs '0027!', '0028!	1-22
A	MUROTA J ET AL: "LOW-TEMPERATURE EPITAXIAL GROWTH OF SI/Si1-XGEX/SI HETEROSTRUCTURE BY CHEMICAL VAPOR DEPOSITION" JAPANESE JOURNAL OF APPLIED PHYSICS, PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS. TOKYO, JP, vol. 33, no. 4B, PART 1, 1 April 1994 (1994-04-01), pages 2290-2299, XP000595134 ISSN: 0021-4922 2. Ultraclean Low-Pressure CVD Processing; Figure 2	1-22
E	EP 1 315 199 A (ETH ZUERICH) 28 May 2003 (2003-05-28) cited in the application the whole document	1-22

INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No

PCT/EP 03/03136

Patent document cited in search report		Publication date		Patent family member(s)	Publication date
US 2002056414	A1	16-05-2002	KR	2002029190 A	18-04-2002
US 2002139996	A1	03-10-2002	JP	2002324805 A	08-11-2002
EP 1315199	A	28-05-2003	EP	1315199 A1	28-05-2003
			WO	03044839 A2	30-05-2003